

The tight-binding model and low-energy effective model

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Outline

Tight binding method

Band structure

Second quantization

Single-layer and bilayer graphene

Summary

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Tight binding method

Band structure

Second quantization

Single-layer and bilayer graphene

Summary

What is tight binding model

Why band structure happens:

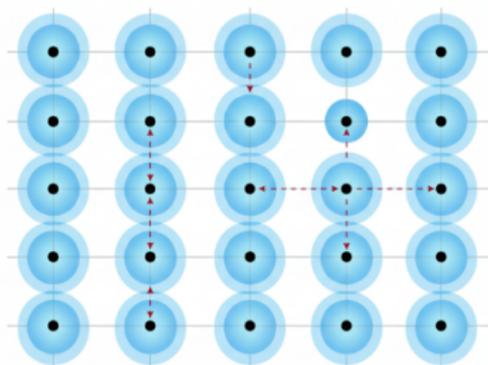
- The electrons of isolated atom occupy atomic orbitals with **discrete** energy levels
- If two atoms come close enough \rightarrow their atomic orbitals **overlap** \rightarrow electrons can tunnel between the atoms
- This tunneling **splits** the atomic orbitals into molecular orbitals with different energies
- If a large number N of identical atoms come together to form a solid \rightarrow Each discrete energy level splits into N levels, each with different energy

$$N \sim 10^{22}$$

- The adjacent levels are very closely spaced in energy \rightarrow it can be considered to form a **continuum (energy band)**

What is tight binding model

- An approach to calculate band structure in solids
- The name “tight binding” suggests that the model describes the properties of **tightly bound** electrons in solids
- The electrons should have **limited interaction** with states on surrounding atoms of the solid



Why tight binding model

- When the number of atoms/electrons is very small ($N < 10$) → exact method

Calculations resource increase exponentially as N increases. And it become impossible

- $N < \text{a few thousand atoms}$ → density functional theory techniques
- $N > 10000$ → self-consistent DFT calculation is also impossible

Linear combination of atomic orbitals

$$H(\mathbf{r}) = H_{\text{at}}(\mathbf{r}) + \sum_{n \neq 0} V(\mathbf{r} - \mathbf{R}_n) = H_{\text{at}}(\mathbf{r}) + \Delta U(\mathbf{r})$$

Schrödinger equation

$$H\psi_m(\mathbf{r}) = \varepsilon_m\psi_m(\mathbf{r}) \leftarrow \text{Difficult to solve}$$

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- $V(\mathbf{r} - \mathbf{R}_n)$: atomic potentials at site \mathbf{R}_n
- ΔU is small enough
- Atomic orbitals $\varphi_m(\mathbf{r})$ are eigenstates of $H_{\text{at}}(\mathbf{r})$

$$H_{\text{at}}\varphi_m(\mathbf{r}) = \varepsilon_m\varphi_m(\mathbf{r})$$

- Linear combination of atomic orbitals (LCAO)

$$\psi_m(\mathbf{r}) = \sum_n b_m(\mathbf{R}_n)\varphi_m(\mathbf{r} - \mathbf{R}_n)$$

Bloch band

The Bloch theorem

$$\psi(\mathbf{r} + \mathbf{R}_l) = e^{i\mathbf{k} \cdot \mathbf{R}_l} \psi(\mathbf{r})$$

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$$\sum_p b_m(\mathbf{R}_p + \mathbf{R}_l) \varphi_m(\mathbf{r} - \mathbf{R}_p) = e^{i\mathbf{k} \cdot \mathbf{R}_l} \sum_n b_m(\mathbf{R}_n) \varphi_m(\mathbf{r} - \mathbf{R}_n)$$

Bloch band

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$$\sum_n b_m(\mathbf{R}_n + \mathbf{R}_l) \varphi_m(\mathbf{r} - \mathbf{R}_n) = e^{i\mathbf{k} \cdot \mathbf{R}_l} \sum_n b_m(\mathbf{R}_n) \varphi_m(\mathbf{r} - \mathbf{R}_n)$$

Consequently

$$b_m(\mathbf{R}_n + \mathbf{R}_l) = e^{i\mathbf{k} \cdot \mathbf{R}_l} b_m(\mathbf{R}_n)$$

Tight-binding method

$$b_m(\mathbf{R}_n + \mathbf{R}_l) = e^{i\mathbf{k}\cdot\mathbf{R}_l} b_m(\mathbf{R}_n)$$

- $\mathbf{R}_n = 0 \rightarrow b_m(\mathbf{R}_l) = e^{i\mathbf{k}\cdot\mathbf{R}_l} b_m(0)$
- Normalization condition

$$\begin{aligned} 1 &= \int d\mathbf{r} \psi_m^*(\mathbf{r}) \psi_m(\mathbf{r}) = \sum_{n,l} \int d\mathbf{r} b_m^*(0) e^{-i\mathbf{k}\cdot\mathbf{R}_n} b_m(0) e^{i\mathbf{r}\cdot\mathbf{R}_l} \varphi_m^*(\mathbf{r} - \mathbf{R}_n) \varphi_m(\mathbf{r} - \mathbf{R}_l) \\ &= \sum_{n,l} e^{-i\mathbf{k}\cdot(\mathbf{R}_n - \mathbf{R}_l)} b_m^*(0) b_m(0) \int d\mathbf{r} \varphi_m^*(\mathbf{r} - \mathbf{R}_n) \varphi_m(\mathbf{r} - \mathbf{R}_l) \\ &= \sum_l \sum_p e^{-i\mathbf{k}\cdot\mathbf{R}_p} b_m^*(0) b_m(0) \int d\mathbf{x} \varphi_m^*(\mathbf{x} - \mathbf{R}_p) \varphi_m(\mathbf{x}) \\ &= N \sum_p e^{-i\mathbf{k}\cdot\mathbf{R}_p} b_m^*(0) b_m(0) \int d\mathbf{x} \varphi_m^*(\mathbf{x} - \mathbf{R}_p) \varphi_m(\mathbf{x}) \end{aligned}$$

In the above derivation, we set $\mathbf{x} = \mathbf{r} - \mathbf{R}_l$.

Tight-binding method

$$1 = Nb_m^*(0)b_m(0) + N \sum_{p \neq 0} e^{-i\mathbf{k} \cdot \mathbf{R}_p} b_m^*(0)b_m(0) \int d\mathbf{x} \varphi_m^*(\mathbf{x} - \mathbf{R}_p)\varphi_m(\mathbf{x})$$

- Since we assume ΔU is small, the overlap of atomic orbitals can be safely neglected

And thus

$$b_m(0) \approx \frac{1}{\sqrt{N}}$$

and

$$\psi_m(\mathbf{r}) \approx \frac{1}{\sqrt{N}} \sum_n e^{i\mathbf{k} \cdot \mathbf{R}_n} \varphi_m(\mathbf{r} - \mathbf{R}_n)$$

Tight-binding method

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And thus

$$b_m(0) \approx \frac{1}{\sqrt{N}}$$

and

$$\psi_m(\mathbf{r}) \approx \frac{1}{\sqrt{N}} \sum_{\mathbf{R}} e^{i\mathbf{k} \cdot \mathbf{R}} \varphi_m(\mathbf{r} - \mathbf{R})$$

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Band structure

Only consider the s -orbitals

$$\psi(\mathbf{r}) = \frac{1}{\sqrt{N}} \sum_{\mathbf{R}} e^{i\mathbf{k}\cdot\mathbf{R}} \phi_s(\mathbf{r} - \mathbf{R})$$

- Dispersion relation

$$\begin{aligned} E(\mathbf{k}) &= \int \psi^*(\mathbf{r}) H \psi(\mathbf{r}) d\mathbf{r} \\ &= \frac{1}{N} \sum_{\mathbf{R}, \mathbf{R}'} e^{i\mathbf{k}\cdot(\mathbf{R}' - \mathbf{R})} \int d\mathbf{r} \phi_s^*(\mathbf{r} - \mathbf{R}) H \phi_s(\mathbf{r} - \mathbf{R}') \\ &= \frac{1}{N} \sum_{\mathbf{R}, \mathbf{R}'} e^{i\mathbf{k}\cdot(\mathbf{R}' - \mathbf{R})} \int d\mathbf{x} \phi_s^*(\mathbf{x}) H \phi_s(\mathbf{x} - (\mathbf{R}' - \mathbf{R})) \\ &= \sum_{\mathbf{R}'} e^{i\mathbf{k}\cdot\mathbf{R}''} \int d\mathbf{x} \phi_s^*(\mathbf{x}) H \phi_s(\mathbf{x} - \mathbf{R}'') \\ &= \sum_{\mathbf{R}} e^{i\mathbf{k}\cdot\mathbf{R}} \int d\mathbf{x} \phi_s^*(\mathbf{x}) H \phi_s(\mathbf{x} - \mathbf{R}) \end{aligned}$$

Band structure

$$E(\mathbf{k}) = \sum_{\mathbf{R}} e^{i\mathbf{k}\cdot\mathbf{R}} \int d\mathbf{x} \phi_s^*(\mathbf{x}) H \phi_s(\mathbf{x} - \mathbf{R})$$

- \mathbf{R} sums over all translation vector
- $\mathbf{R} = 0$ gives the s -orbital energy in isolated atom

$$\int d\mathbf{x} \phi_s^*(\mathbf{x}) H \phi_s(\mathbf{x}) = \varepsilon_s$$

- Hopping energy

$$\sum_{\mathbf{R}} e^{i\mathbf{k}\cdot\mathbf{R}} T(|\mathbf{R}|)$$

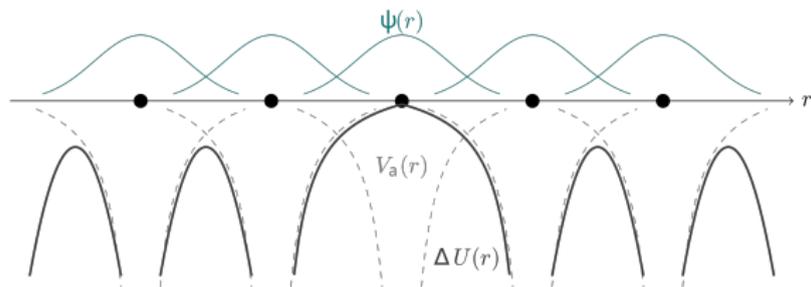
- For the s -orbital band

$$T(|\mathbf{R}|) = A e^{-\alpha R^2/R^2}$$

Single band in 1D crystal

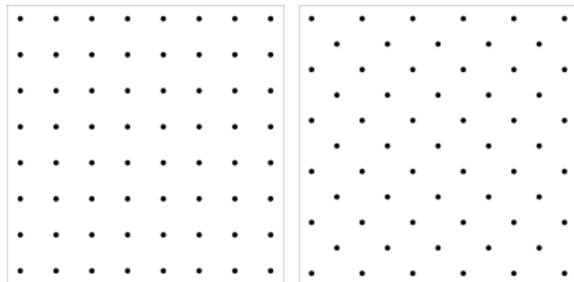
In a 1D crystal, the translation vectors $\mathbf{R} = na_0\hat{\mathbf{x}}$, where n is an integer

$$E(k) = \varepsilon_s + \left(e^{ika_0} + e^{-ika_0} \right) T(a_0) + \left(e^{2ika_0} + e^{-2ika_0} \right) T(2a_0) + \dots$$
$$\approx \varepsilon_0 + 2 \cos(ka_0) T(a_0)$$



$T(2a_0)$ can be ignored since the overlap of the wavefunction in the next-nearest-neighbor is exponential small

Single band in 2D/3D crystal



With nearest hopping

$$E(k_x, k_y) = \varepsilon_s + 2T(a) \cos(k_x a) + 2T(b) \cos(k_y b)$$

N -atom basis

In a crystal with an N atom basis, the states can be expanded as combination of N Bloch states,

$$\psi_{m,\mathbf{k}}(\mathbf{r}) = \sum_i c_{i,\mathbf{k}} \phi_{i,\mathbf{k}}(\mathbf{r}) = \sum_i c_{i,\mathbf{k}} \frac{1}{\sqrt{N}} \sum_{\mathbf{R}_i} e^{i\mathbf{k}\cdot\mathbf{R}_i} \phi(\mathbf{r} - \mathbf{R}_i)$$

The energy

$$\begin{aligned} E(\mathbf{k}) &= \sum_{i,j} c_{i,\mathbf{k}}^* c_{j,\mathbf{k}} \phi_{i,\mathbf{k}}^*(\mathbf{r}) H \phi_{j,\mathbf{k}}(\mathbf{r}) \\ &= \sum_{i,j} c_{i,\mathbf{k}}^* \langle \phi_{i,\mathbf{k}} | H | \phi_{j,\mathbf{k}} \rangle c_{j,\mathbf{k}} \\ &= (c_{1,\mathbf{k}}^* \quad c_{2,\mathbf{k}}^* \quad \dots) \langle \phi_{i,\mathbf{k}} | H | \phi_{j,\mathbf{k}} \rangle \begin{pmatrix} c_{1,\mathbf{k}} \\ c_{2,\mathbf{k}} \\ \vdots \end{pmatrix} \end{aligned}$$

We should find the lowest energy to determine the coefficient $c_{i,\mathbf{k}}$

N -atom basis

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The Hamiltonian is expanded in the basis of $\phi_{i,\mathbf{k}}(\mathbf{r})$

$$H_{ij} = \langle \phi_{i,\mathbf{k}} | H | \phi_{j,\mathbf{k}} \rangle$$

Finally, the energy structure can be determined by the equation

$$\det(H - E(\mathbf{k})I) = 0$$

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Second quantization

$$\Psi(\mathbf{r}) = \sum_m a_m \psi_m(\mathbf{r}), \quad \psi_m(\mathbf{r}) = \sum_n b_m(\mathbf{R}_n) \varphi_m(\mathbf{r} - \mathbf{R}_n)$$

In second quantization, the basic object is the field operator

$$\Psi(\mathbf{r}) = \sum_{m,n} a_m b_m(\mathbf{R}_n) \varphi_m(\mathbf{r} - \mathbf{R}_n) \rightarrow \sum_{m,n} c_m(\mathbf{R}_n) \varphi_m(\mathbf{r} - \mathbf{R}_n)$$

Second quantization

$$\Psi(\mathbf{r}) = \sum_m a_m \psi_m(\mathbf{r}), \quad \psi_m(\mathbf{r}) = \sum_n b_m(\mathbf{R}_n) \varphi_m(\mathbf{r} - \mathbf{R}_n)$$

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$$\hat{\Psi}(\mathbf{r}) = \sum_{m,n} \hat{c}_m(\mathbf{R}_n) \varphi_m(\mathbf{r} - \mathbf{R}_n)$$

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The Hamiltonian in second quantization

$$\begin{aligned} \hat{H} &= \int d\mathbf{r} \hat{\Psi}^\dagger(\mathbf{r}) H \hat{\Psi}(\mathbf{r}) \\ &= \sum_{i,j,m} t_{ij}^{mn} c_m^\dagger(\mathbf{R}_i) c_n(\mathbf{R}_j) \end{aligned}$$

The hopping coefficient

$$t_{ij}^{mn} = \int d\mathbf{r} \varphi_m^*(\mathbf{r} - \mathbf{R}_i) H \varphi_n(\mathbf{r} - \mathbf{R}_j)$$

Outline

Tight binding method

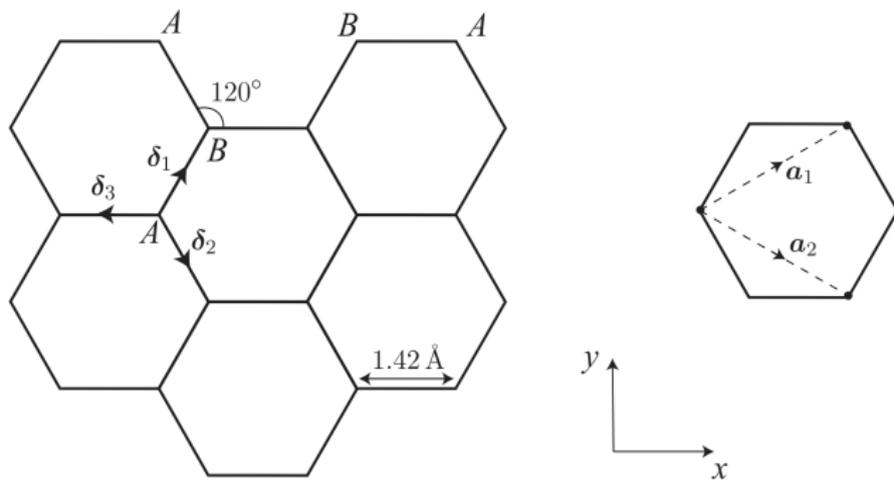
Band structure

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Single-layer and bilayer graphene

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Tight-binding model in single layer graphene



From Leggett's lecture

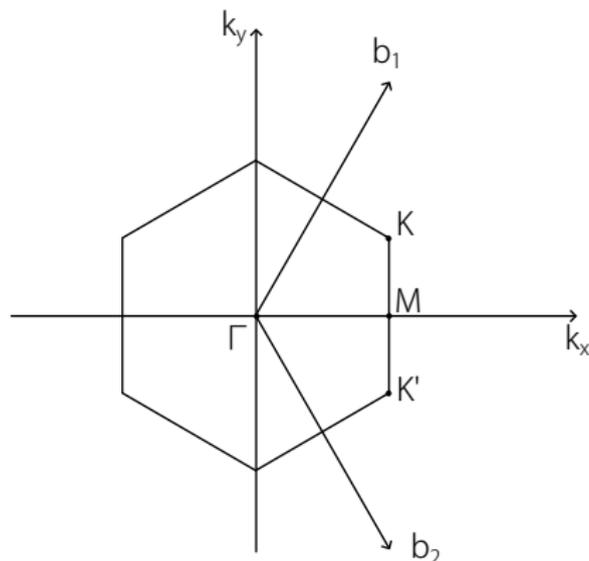
$$\mathbf{a}_1 = \frac{a}{2} (3, \sqrt{3}), \quad \mathbf{a}_2 = \frac{a}{2} (3, -\sqrt{3})$$

The reciprocal lattice vectors \mathbf{b}_1 , \mathbf{b}_2 defined by $\mathbf{a}_i \cdot \mathbf{b}_j = 2\pi\delta_{ij}$:

$$\mathbf{b}_1 = \frac{2\pi}{3a} (1, \sqrt{3}), \quad \mathbf{b}_2 = \frac{2\pi}{3a} (1, -\sqrt{3})$$

Tight-binding model in single layer graphene

First Brillouin zone



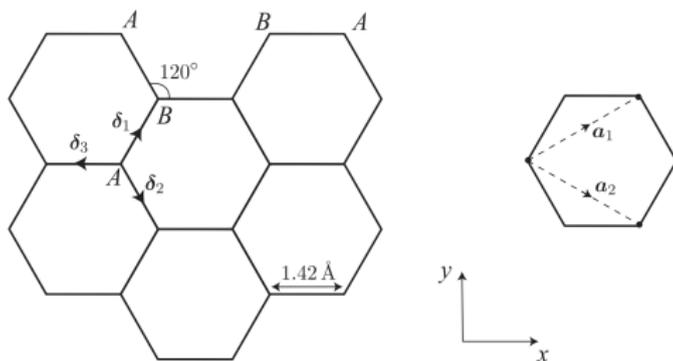
$$\mathbf{K} = \frac{2\pi}{3a} \left(1, \frac{1}{\sqrt{3}} \right), \quad \mathbf{K}' = \frac{2\pi}{3a} \left(1, -\frac{1}{\sqrt{3}} \right), \quad \mathbf{M} = \frac{2\pi}{3a} (1, 0)$$

- The electrons outside Carbon atom: $1s^2 2s^2 2p^2$

Tight-binding model in single layer graphene

Only nearest neighbor hopping is considered

$$H = -t \sum_{\langle ij \rangle} \left(a_i^\dagger b_j + b_j^\dagger a_i \right) = -t \sum_{i \in A} \sum_{\boldsymbol{\delta}} \left(a_i^\dagger b_{i+\boldsymbol{\delta}} + b_{i+\boldsymbol{\delta}}^\dagger a_i \right)$$



$$\boldsymbol{\delta}_1 = \frac{a}{2} \left(1, \sqrt{3} \right), \quad \boldsymbol{\delta}_2 = \frac{a}{2} \left(1, -\sqrt{3} \right), \quad \boldsymbol{\delta}_3 = a \left(-1, 0 \right)$$

Tight-binding model in single layer graphene

Fourier transform

$$a_i = \frac{1}{\sqrt{N/2}} \sum_{\mathbf{k}} e^{-i\mathbf{k}\cdot\mathbf{r}_i} a_{\mathbf{k}}$$

where $N/2$ is the number of A sites.

$$\begin{aligned} H &= -\frac{t}{N/2} \sum_{i \in A} \sum_{\delta, \mathbf{k}, \mathbf{k}'} \left[e^{i(\mathbf{k}-\mathbf{k}')\cdot\mathbf{r}_i} e^{-i\mathbf{k}'\cdot\delta} a_{\mathbf{k}}^\dagger b_{\mathbf{k}'} + \text{H. c.} \right] \\ &= -t \sum_{\delta, \mathbf{k}} \left(e^{-i\mathbf{k}\cdot\delta} a_{\mathbf{k}}^\dagger b_{\mathbf{k}} + \text{H. c.} \right) \\ &= \begin{pmatrix} a_{\mathbf{k}} \\ b_{\mathbf{k}} \end{pmatrix}^\dagger \begin{pmatrix} 0 & \Delta_{\mathbf{k}} \\ \Delta_{\mathbf{k}}^* & 0 \end{pmatrix} \begin{pmatrix} a_{\mathbf{k}} \\ b_{\mathbf{k}} \end{pmatrix} \\ &= -t \sum_{\delta} [\cos(\mathbf{k}\cdot\delta)\sigma_1 - \sin(\mathbf{k}\cdot\delta)\sigma_2] \end{aligned}$$

Tight-binding model in single layer graphene

$$\begin{aligned}\Delta_{\mathbf{k}} &= e^{i\mathbf{k}\cdot\delta_1} + e^{i\mathbf{k}\cdot\delta_2} + e^{i\mathbf{k}\cdot\delta_3} \\ &= e^{-ik_x a} \left[1 + 2e^{i3k_x a/2} \cos\left(\frac{\sqrt{3}}{2}k_y a\right) \right]\end{aligned}$$

The energy spectrum

$$\begin{aligned}E(\mathbf{k}) &= \pm t \sqrt{\Delta_{\mathbf{k}} \Delta_{\mathbf{k}}^*} \\ &= \pm t \sqrt{1 + 4 \cos\left(\frac{3}{2}k_x a\right) \cos\left(\frac{\sqrt{3}}{2}k_y a\right) + 4 \cos^2\left(\frac{\sqrt{3}}{2}k_y a\right)}\end{aligned}$$

- For $\mathbf{k} = \mathbf{K}$ or \mathbf{K}' , $\Delta_{\mathbf{k}} = 0$, gapless bands

Tight-binding model in single layer graphene

$$\Delta_{\mathbf{K}+\mathbf{q}} \approx \Delta(\mathbf{K}) + \left. \frac{\partial \Delta_{\mathbf{k}}}{\partial \mathbf{k}} \right|_{\mathbf{k}=\mathbf{K}} \mathbf{q} = -ie^{-iK_x a} \frac{3a}{2} (q_x + iq_y)$$

Near the Dirac point \mathbf{K} , the Hamiltonian is thus

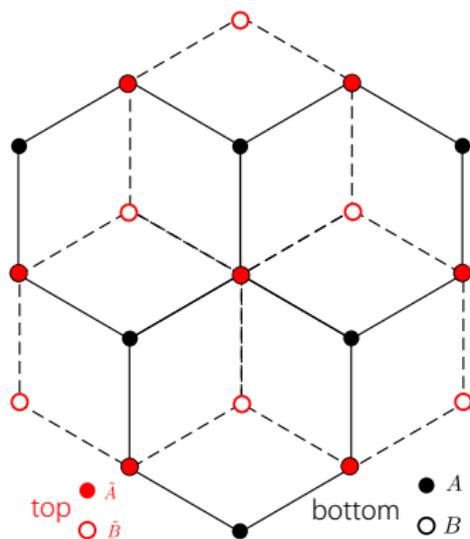
$$H(\mathbf{K} + \mathbf{q}) = v_F \begin{pmatrix} 0 & q_x + iq_y \\ q_x - iq_y & 0 \end{pmatrix} = v_F (q_x \sigma_1 - q_y \sigma_2)$$

Near \mathbf{K}'

$$H(\mathbf{K}' + \mathbf{q}) = v_F \begin{pmatrix} 0 & q_x - iq_y \\ q_x + iq_y & 0 \end{pmatrix} = v_F (q_x \sigma_1 + q_y \sigma_2)$$

Effective model in bilayer graphene

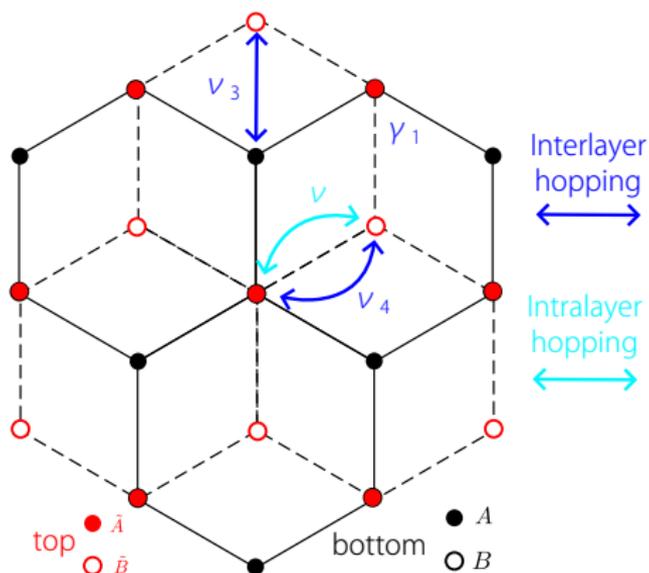
AB-stacking



- Bernal type
- One A atom in the top layer (\tilde{A}) lies above a B atom in the bottom layer

Effective model in bilayer graphene

AB-stacking



- Bernal type
- One A atom in the top layer (\tilde{A}) lies above a B atom in the bottom layer

Effective model in bilayer graphene

$$H = \begin{pmatrix} A & \tilde{B} & \tilde{A} & B \\ 0 & 0 & 0 & \nu\pi^\dagger \\ 0 & 0 & \nu\pi & 0 \\ 0 & \nu\pi^\dagger & 0 & 0 \\ \nu\pi & 0 & 0 & 0 \end{pmatrix} \begin{matrix} A \\ \tilde{B} \\ \tilde{A} \\ B \end{matrix}$$

where $\pi^\dagger = k_x - ik_y$

- No any inter-layer coupling

Effective model in bilayer graphene

$$H = \begin{pmatrix} A & \tilde{B} & \tilde{A} & B \\ 0 & 0 & 0 & \nu\pi^\dagger \\ 0 & 0 & \nu\pi & 0 \\ 0 & \nu\pi^\dagger & 0 & \gamma_1 \\ \nu\pi & 0 & \gamma_1 & 0 \end{pmatrix} \begin{matrix} A \\ \tilde{B} \\ \tilde{A} \\ B \end{matrix}$$

where $\pi^\dagger = k_x - ik_y$

- Coupling between \tilde{A} and B

Effective model in bilayer graphene

$$H = \begin{pmatrix} A & \tilde{B} & \tilde{A} & B \\ 0 & \nu_3 \pi & 0 & \nu \pi^\dagger \\ \nu_3 \pi^\dagger & 0 & \nu \pi & 0 \\ 0 & \nu \pi^\dagger & 0 & \gamma_1 \\ \nu \pi & 0 & \gamma_1 & 0 \end{pmatrix} \begin{matrix} A \\ \tilde{B} \\ \tilde{A} \\ B \end{matrix}$$

where $\pi^\dagger = k_x - ik_y$

- Coupling between \tilde{A} and B
- Coupling between A and \tilde{B}

Effective model in bilayer graphene

$$H = \begin{pmatrix} A & \tilde{B} & \tilde{A} & B \\ 0 & \nu_3 \pi & \nu_4 \pi^\dagger & \nu \pi^\dagger \\ \nu_3 \pi^\dagger & 0 & \nu \pi & \nu_4 \pi \\ \nu_4 \pi & \nu \pi^\dagger & 0 & \gamma_1 \\ \nu \pi & \nu_4 \pi^\dagger & \gamma_1 & 0 \end{pmatrix} \begin{matrix} A \\ \tilde{B} \\ \tilde{A} \\ B \end{matrix}$$

where $\pi^\dagger = k_x - ik_y$

- Coupling between \tilde{A} and B
- Coupling between A and \tilde{B}
- Coupling between A/B and \tilde{A}/\tilde{B}

$$v = 8 \times 10^5 \text{ m/s}, \gamma_1 = 0.39 \text{ eV}$$

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Summary

- Tight-binding model
- Calculate the band spectrum: Band width, band gap
- Surface states, many-body problem and quasiparticle calculations